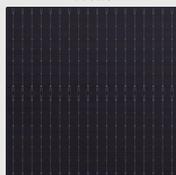


KEY FEATURES

- High Photoelectric Conversion Efficiency
- Higher Power Generation
- Excellent Resistance to Hidden Cracks
- Higher Efficiency in Power Generation



Front



Back

Size : 210mm*210mm±0.25mm

Thickness : 130±13μm

Solderability : ≥0.5N/mm

The results may vary depending to DS,welding methods and conditions.

Technical Data And Design

Power: -0.32%/K

Voltage: -0.26 %/K

Current: +0.046%/K

Front (-): 18 * 0.04 ± 0.03mm main gate line (silver), 120 ± 12 secondary gate lines blue (dark blue), anti-reflective film (silicon nitride)

Back (+): 18 * 0.04 ± 0.03mm Back electrode width (silver) 138± 14 mm sub-grid lines

Rsh≥35Ω, Irev2≤1.0A

Front Electrical Performance Parameters

Eff(%)	FF(%)	Pmpp (W)	I _{mp} (A)	U _{mp} (V)	I _{sc} (A)	U _{oc} (V)
25.8	84.04	11.377	17.887	0.636	18.494	0.732
25.7	83.72	11.333	17.847	0.635	18.494	0.732
25.6	83.39	11.289	17.805	0.634	18.494	0.732
25.5	83.22	11.244	17.764	0.633	18.485	0.731
25.4	83.05	11.200	17.722	0.632	18.474	0.730
25.3	82.87	11.156	17.680	0.631	18.467	0.729
25.2	82.71	11.112	17.638	0.630	18.454	0.728
25.1	82.53	11.068	17.596	0.629	18.447	0.727
25.0	82.35	11.024	17.554	0.628	18.439	0.726
24.9	82.19	10.980	17.512	0.627	18.427	0.725
24.8	82.01	10.936	17.469	0.626	18.418	0.724
24.7	81.88	10.892	17.426	0.625	18.398	0.723

Iv Curve

